

COMPLEMENTARY PAIR ENHANCEMENT MODE MOSFET

Product Summary

Device	$V_{(BR)DSS}$	$R_{DS(on)}$	I_D $T_A = 25^\circ C$
Q1	30V	60m Ω @ $V_{GS} = 10V$	3.4A
		100m Ω @ $V_{GS} = 4.5V$	2.7A
Q2	-30V	95m Ω @ $V_{GS} = -10V$	-2.8A
		140m Ω @ $V_{GS} = -4.5V$	-2.3A

Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

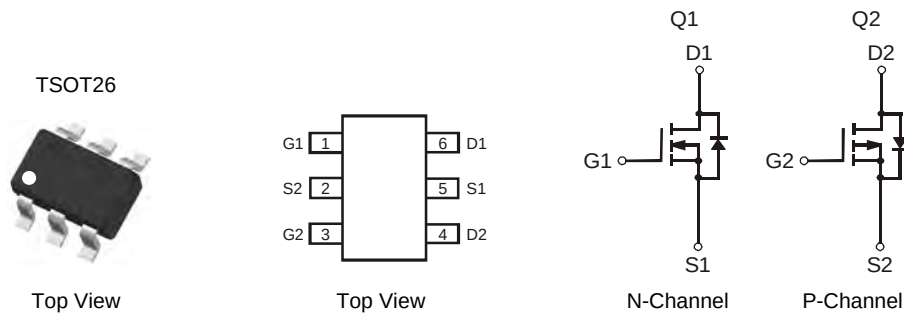
- Backlighting
- DC-DC Converters
- Power management functions

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free Finish; RoHS compliant (Note 1)**
- **Halogen and Antimony Free. "Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish – Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.013 grams (approximate)

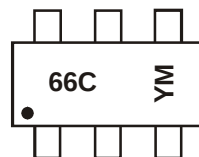


Ordering Information (Note 3)

Part Number	Case	Packaging
DMG6602SVT-7	TSOT26	3000 / Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 3. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information



66C = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: X = 2010)
M = Month (ex: 9 = September)

Date Code Key

Year	2010	2011	2012	2013	2014	2015	2016	2017
Code	X	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings – Q1 @TA = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 5) $V_{GS} = 10V$	Steady State	$T_A = 25^{\circ}C$	I_D	3.4	A
		$T_A = 70^{\circ}C$		2.7	
Continuous Drain Current (Note 5) $V_{GS} = 4.5V$	Steady State	$T_A = 25^{\circ}C$	I_D	2.7	A
		$T_A = 70^{\circ}C$		2.2	
Maximum Continuous Body Diode Forward Current (Note 5)			I_S	1.5	A
Pulsed Drain Current (Note 5)			I_{DM}	25	A

Maximum Ratings – Q2 @TA = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 5) V _{GS} = -10V	Steady State	T _A = 25°C T _A = 70°C	I _D	-2.8 -2.4	A
Continuous Drain Current (Note 5) V _{GS} = -4.5V	Steady State	T _A = 25°C T _A = 70°C	I _D	-2.3 -2.1	A
Maximum Continuous Body Diode Forward Current (Note 5)			I _S	-1.5	A
Pulsed Drain Current (Note 5)			I _D	-20	A

Thermal Characteristics

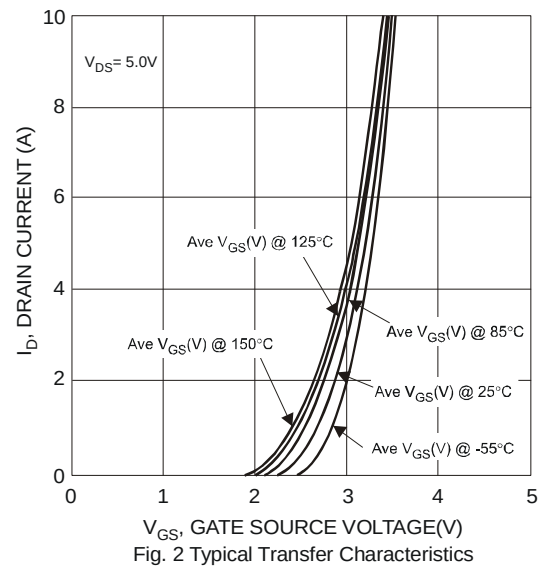
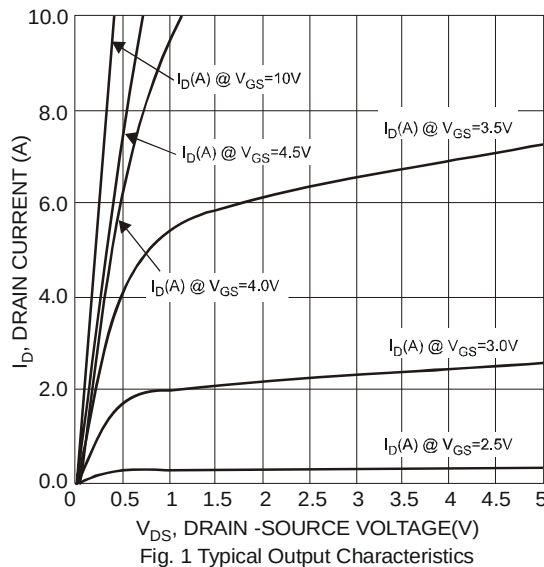
Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 4)	$T_A = 25^\circ C$	P_D	0.84	W
	$T_A = 70^\circ C$		0.52	
Thermal Resistance, Junction to Ambient (Note 4)	Steady state	$R_{\theta JA}$	155	$^\circ C/W$
	$t < 10s$		109	
Total Power Dissipation (Note 5)	$T_A = 25^\circ C$	P_D	1.27	W
	$T_A = 70^\circ C$		0.8	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	$R_{\theta JA}$	102	$^\circ C/W$
	$t < 10s$		71	
Thermal Resistance, Junction to Case (Note 5)		$R_{\theta JC}$	34	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ C$

- Notes:
4. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

Electrical Characteristics – Q1 NMOS @ T_A = 25°C unless otherwise stated

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1.0	μA	V _{DS} = 24V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(th)}	1.0	-	2.3	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(on)}	-	38	60	mΩ	V _{GS} = 10V, I _D = 3.1A
			55	100		V _{GS} = 4.5V, I _D = 2A
Forward Transfer Admittance	Y _{fs}	-	4	-	S	V _{DS} = 5V, I _D = 3.1A
Diode Forward Voltage	V _{SD}	-	0.8	1	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	-	290	400	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.2MHz
Output Capacitance	C _{oss}	-	40	80		
Reverse Transfer Capacitance	C _{rss}	-	40	80		
Gate Resistance	R _g	-	1.4	-	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	-	4	6	nC	V _{DS} = 15V, V _{GS} = 4.5V, I _D = 3.1A
Total Gate Charge (V _{GS} = 10V)	Q _g	-	9	13		
Gate-Source Charge	Q _{gs}	-	1.2	-		
Gate-Drain Charge	Q _{gd}	-	1.5	-	ns	V _{DS} = 15V, V _{GS} = 10V, I _D = 3A
Turn-On Delay Time	t _{D(on)}	-	3	-		
Turn-On Rise Time	t _r	-	5	-		
Turn-Off Delay Time	t _{D(off)}	-	13	-		
Turn-Off Fall Time	t _f	-	3	-		

Notes: 6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to product testing.



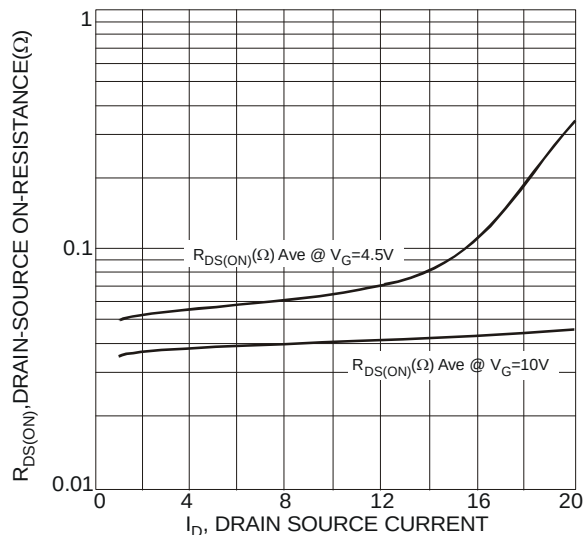


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

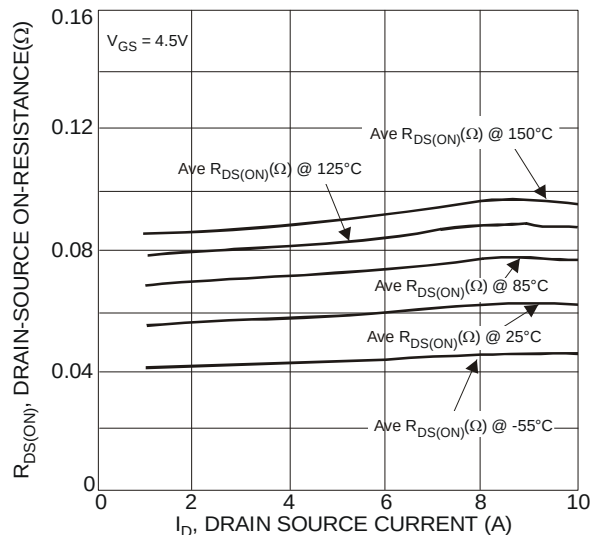


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

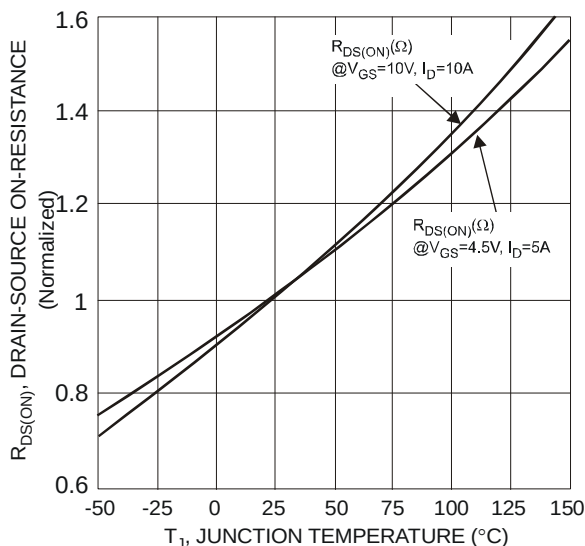


Fig. 5 On-Resistance Variation with Temperature

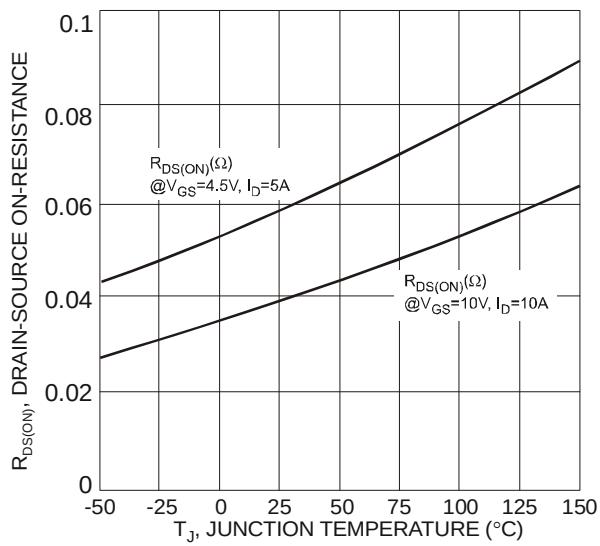


Fig. 6 On-Resistance Variation with Temperature

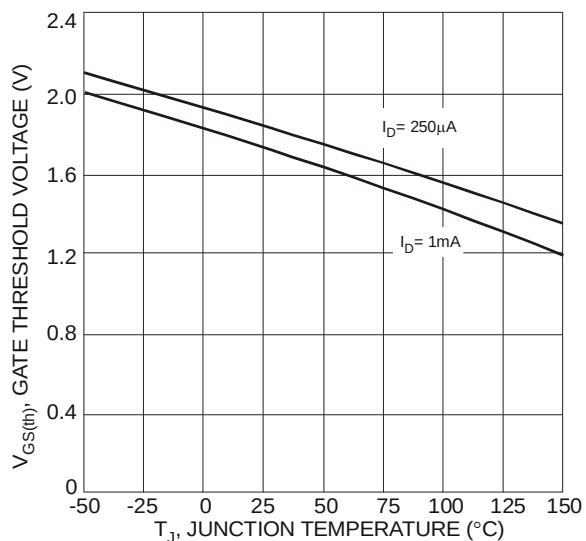


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

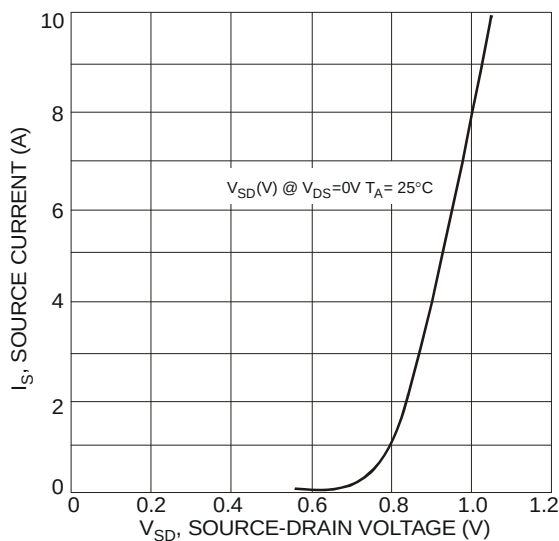
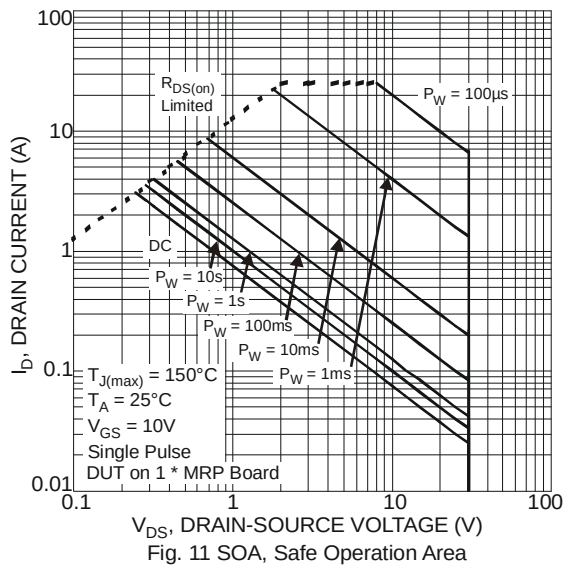
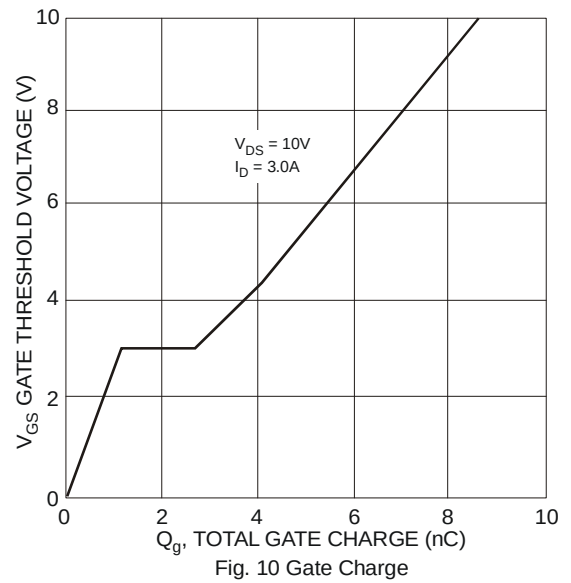
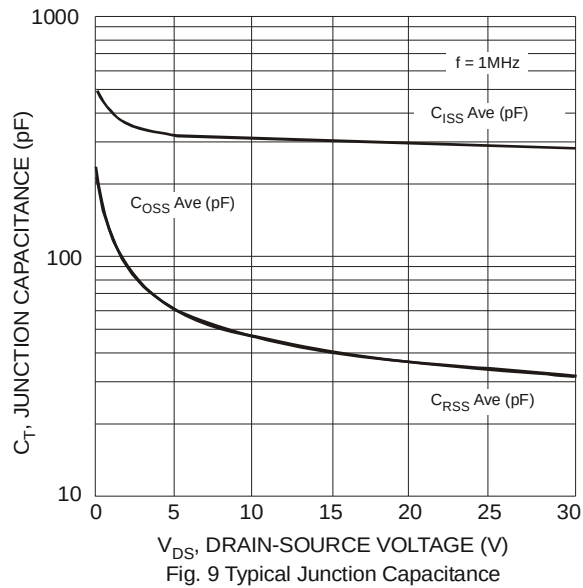


Fig. 8 Diode Forward Voltage vs. Current



Electrical Characteristics – Q2 PMOS @ $T_A = 25^\circ\text{C}$ unless otherwise stated

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	-	-	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	I_{DSS}	-	-	-1.0	μA	$V_{DS} = -24V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	-	-	± 100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(th)}$	-1.0	-	-2.3	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
Static Drain-Source On-Resistance	$R_{DS(on)}$	-	73 99	95 140	m Ω	$V_{GS} = -10V, I_D = -2.7A$ $V_{GS} = -4.5V, I_D = -2A$
Forward Transfer Admittance	$ Y_{fs} $	-	6	-	S	$V_{DS} = -5V, I_D = -2.7A$
Diode Forward Voltage	V_{SD}	-	-0.8	-1.0	V	$V_{GS} = 0V, I_S = -1A$
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{iss}	-	350	420	pF	$V_{DS} = -15V, V_{GS} = 0V,$ $f = 1.2\text{MHz}$
Output Capacitance	C_{oss}	-	50	100		
Reverse Transfer Capacitance	C_{rss}	-	45	80		
Gate Resistance	R_g	-	17.1	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1\text{MHz}$
Total Gate Charge ($V_{GS} = -4.5V$)	Q_g	-	4	6	nC	$V_{DS} = -15V, V_{GS} = -4.5V, I_D = -3A$
Total Gate Charge ($V_{GS} = -10V$)	Q_g	-	7	9		
Gate-Source Charge	Q_{gs}	-	0.9	-		
Gate-Drain Charge	Q_{gd}	-	1.2	-	ns	$V_{DS} = -15V, V_{GS} = -10V, I_D = -3A$
Turn-On Delay Time	$t_{D(on)}$	-	4.8	-		
Turn-On Rise Time	t_r	-	7.3	-		
Turn-Off Delay Time	$t_{D(off)}$	-	20	-		
Turn-Off Fall Time	t_f	-	13	-		

Notes: 6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to production testing.

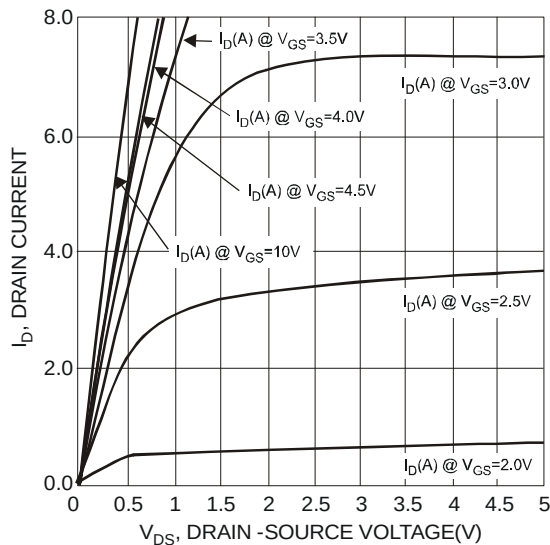


Fig. 12 Typical Output Characteristics

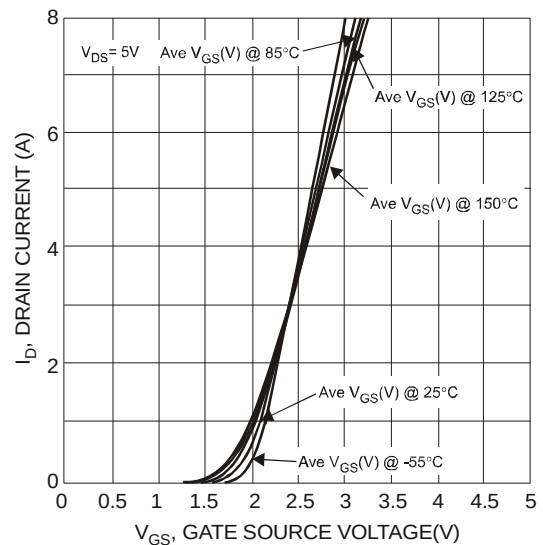


Fig. 13 Typical Transfer Characteristics

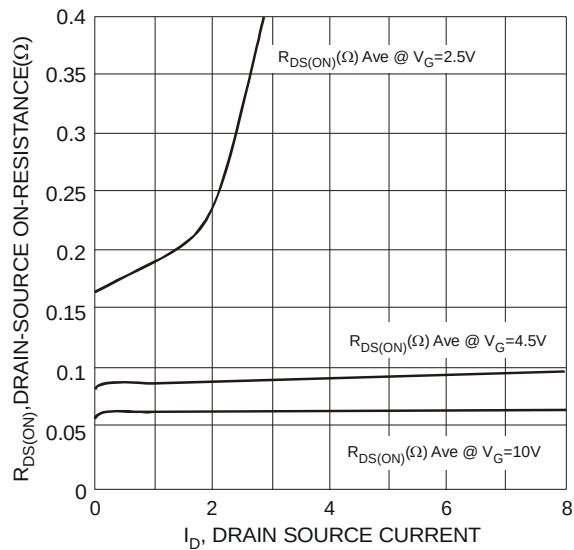


Fig. 14 Typical On-Resistance vs. Drain Current and Gate Voltage

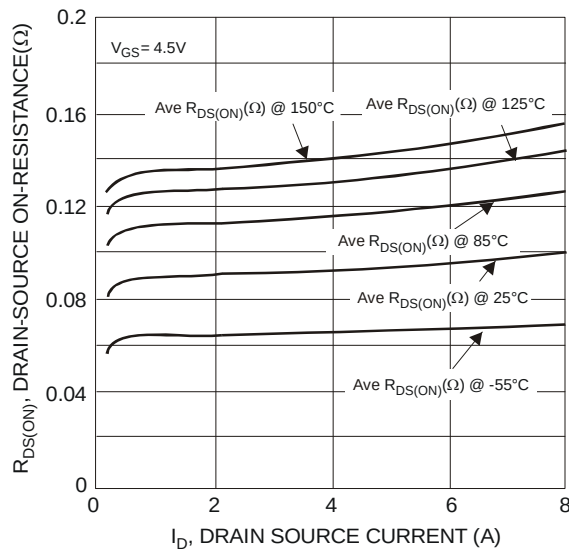


Fig. 15 Typical On-Resistance vs. Drain Current and Temperature

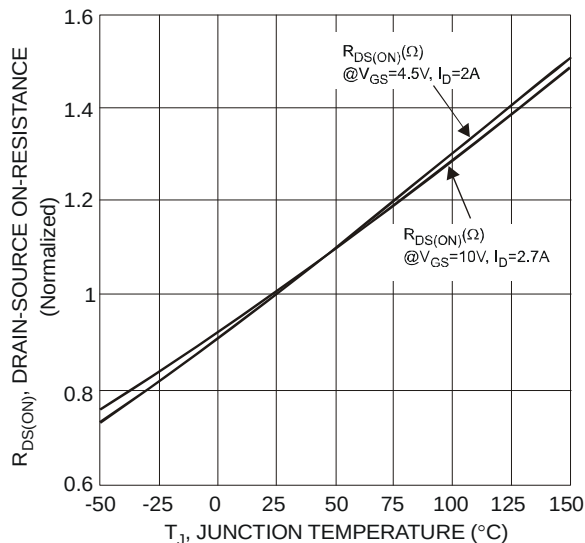


Fig. 16 On-Resistance Variation with Temperature

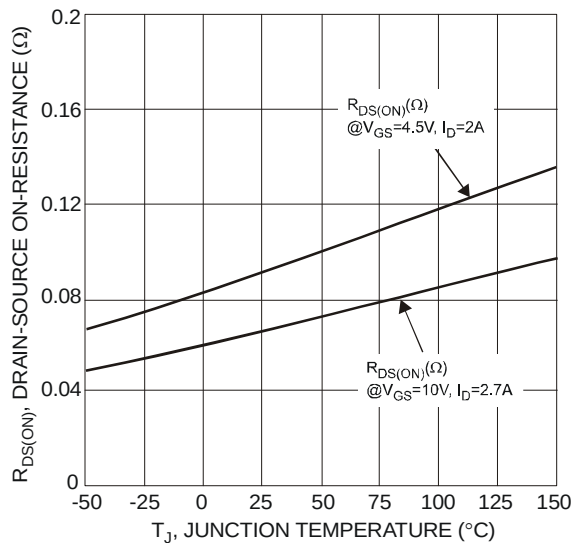


Fig. 17 On-Resistance Variation with Temperature

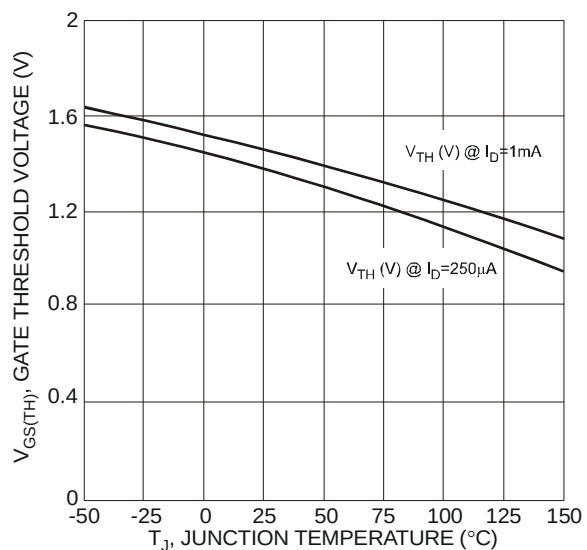


Fig. 18 Gate Threshold Variation vs. Ambient Temperature

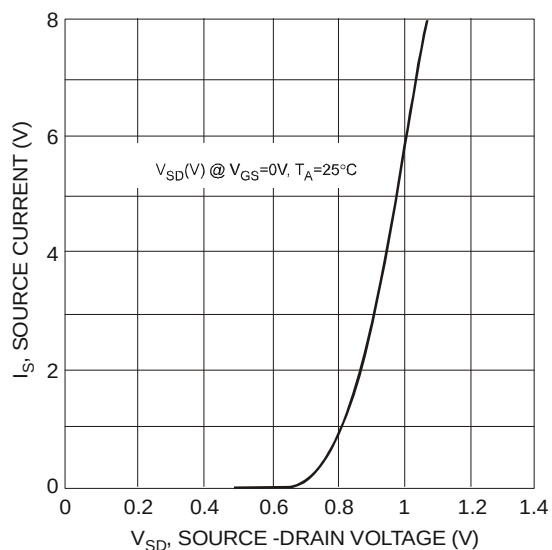
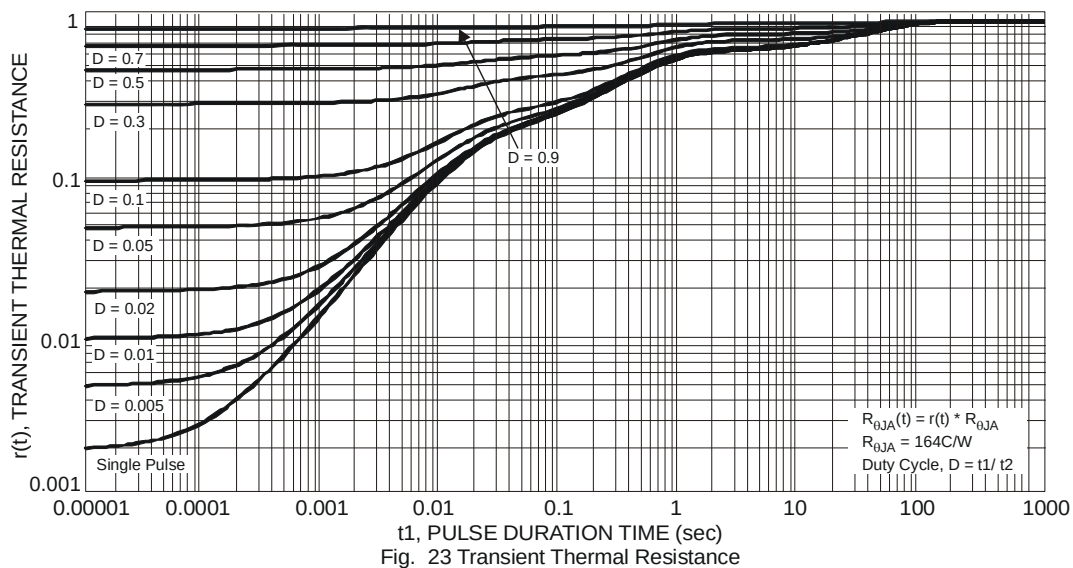
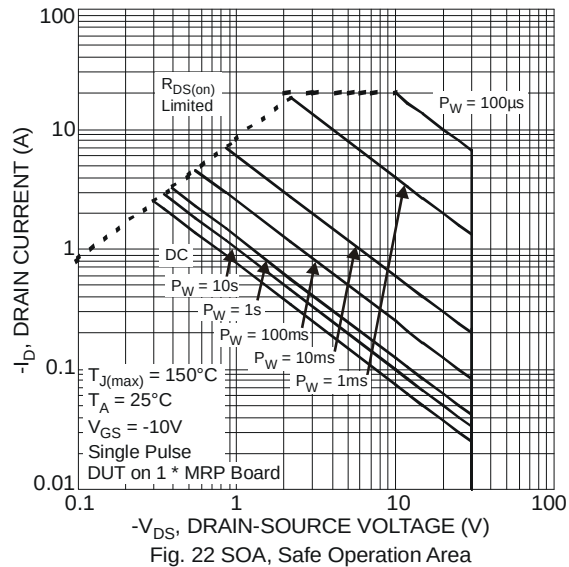
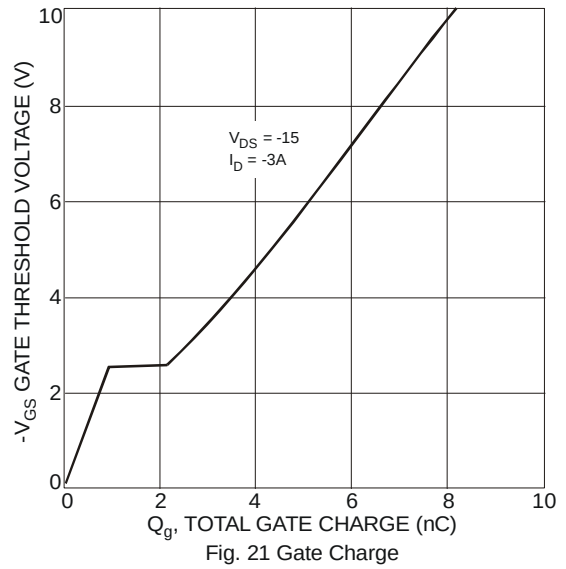
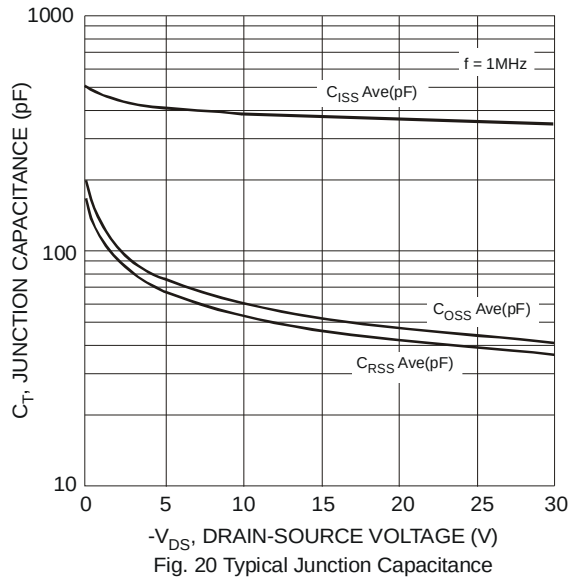
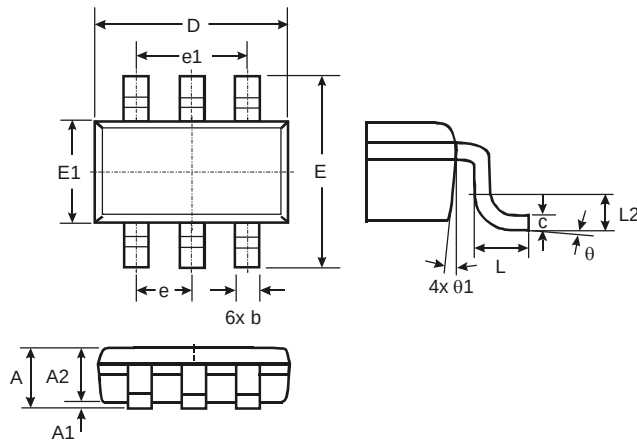


Fig. 19 Diode Forward Voltage vs. Current

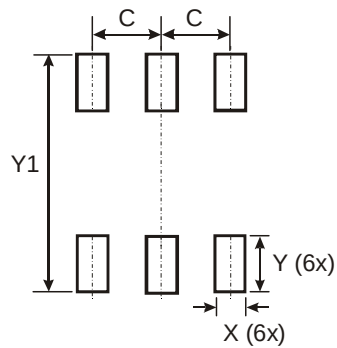


Package Outline Dimensions



TSOT26			
Dim	Min	Max	Typ
A	—	1.00	—
A1	0.01	0.10	—
A2	0.84	0.90	—
D	—	—	2.90
E	—	—	2.80
E1	—	—	1.60
b	0.30	0.45	—
c	0.12	0.20	—
e	—	—	0.95
e1	—	—	1.90
L	0.30	0.50	—
L2	—	—	0.25
θ	0°	8°	4°
θ1	4°	12°	—
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
C	0.950
X	0.700
Y	1.000
Y1	3.199

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